

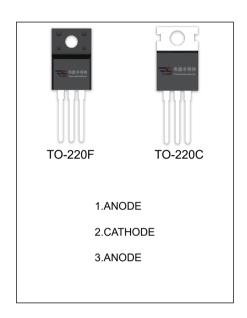
SBD30130SCTB SBDF30130SCTB SCHOTTKY BARRIER RECTIFIER

MAIN CHARACTERISTICS

| Io | 30 (2×15) A |
|----------------|------------------|
| V_{RRM} | 130 V |
| T _j | 150 ℃ |
| $V_{F(typ)}$ | 0.66V (@Tj=125℃) |

FEATURES

- Low Power Loss, High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

| Cymphal | Parameter | SBD | | Heit | |
|---------------------|--|----------|------------|------------|--|
| Symbol | Parameter | | F30130SCTB | Unit | |
| V_{RRM} | Peak repetitive reverse voltage | | | | |
| V_{RWM} | Working peak reverse voltage 130 | | 0 | V | |
| V_R | DC blocking voltage | | | | |
| V _{R(RMS)} | RMS reverse voltage | 91 | | V | |
| lo | Average rectified output current | 30 | | Α | |
| I _{FSM} | Non-Repetitive peak forward surge current (8.3ms half sine wave) | 200 | | Α | |
| R _{OJc} | Thermal resistance from junction to case ,Tc=25℃ | 2.0 | 3.0 | °C/W | |
| R _{OJA} | Thermal resistance from junction to ambient | 62.5 | | °C/W | |
| Tj | Junction temperature | 150 | | $^{\circ}$ | |
| T _{stg} | Storage temperature | -55~+150 | | $^{\circ}$ | |

ELECTRICAL CHARACTERISTICS (T₂=25℃ unless otherwise specified)

| Parameter | Symbol | Test conditions | | Min | Тур | Max | Unit V |
|-----------------|-------------------|----------------------|----------|-----|------|------|-----------|
| Reverse voltage | V _(BR) | | | 130 | | | |
| Reverse current | I _R | V _R =130V | Tj =25℃ | | 15 | 100 | uA |
| | | | Tj =125℃ | | 10 | | mA |
| Forward voltage | V _F | I _F =10A | Tj =25℃ | | 0.66 | | V |
| | | | Tj =125℃ | | 0.59 | | V |
| | | I _F =15A | Tj =25℃ | | 0.78 | 0.82 | V |
| | | | Tj =125℃ | | 0.66 | | V |

^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.



